

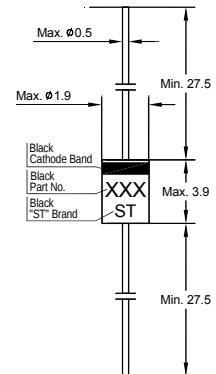
1SS106

SILICON SCHOTTKY BARRIER DIODE

for various detector, high speed switching

Features

- Detection efficiency is very good.
- Small temperature coefficient.
- High reliability with glass seal.



Glass Case DO-35
Dimensions in mm

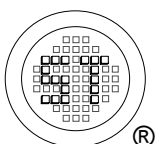
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Average Forward Current	I_O	30	mA
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

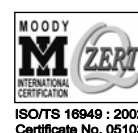
Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	I_F	4.5	-	mA
Reverse Current at $V_R = 6\text{ V}$	I_R	-	70	μA
Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C	-	1.5	pF
Rectifier Efficiency at $V_{in} = 2\text{ Vrms}$, $f = 40\text{ MHz}$, $R_L = 5\text{ K}\Omega$, $C_L = 20\text{ pF}$	η	70	-	%
ESD Capability ¹⁾ at $C = 200\text{ pF}$, both forward and reverse direction 1 pulse.	-	100	-	V

¹⁾ Failure criterion: $I_R \geq 140\text{ }\mu\text{A}$ at $V_R = 6\text{ V}$



SEMTECH ELECTRONICS LTD.

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